



VNQ830M

QUAD CHANNEL HIGH SIDE DRIVER

PRELIMINARY DATA

TYPE	$R_{DS(on)}$	I_{OUT}	V_{CC}
VNQ830M	60 m Ω (*)	6 A (*)	36 V

(*) Per each channel

- CMOS COMPATIBLE INPUTS
- OPEN DRAIN STATUS OUTPUTS
- ON STATE OPEN LOAD DETECTION
- OFF STATE OPEN LOAD DETECTION
- SHORTED LOAD PROTECTION
- UNDERVOLTAGE AND OVERVOLTAGE SHUTDOWN
- LOSS OF GROUND PROTECTION
- VERY LOW STAND-BY CURRENT
- REVERSE BATTERY PROTECTION (**)



DESCRIPTION

The VNQ830M is a quad HSD formed by assembling two VND830M chips in the same SO-28 package. The VND830M is a monolithic device made by using STMicroelectronics VIPower M0-3 Technology. The VNQ830M is intended for driving any type of multiple loads with one side connected to ground.

Active V_{CC} pin voltage clamp protects the device against low energy spikes (see ISO7637 transient

compatibility table). Active current limitation combined with thermal shutdown and automatic restart protects the device against overload.

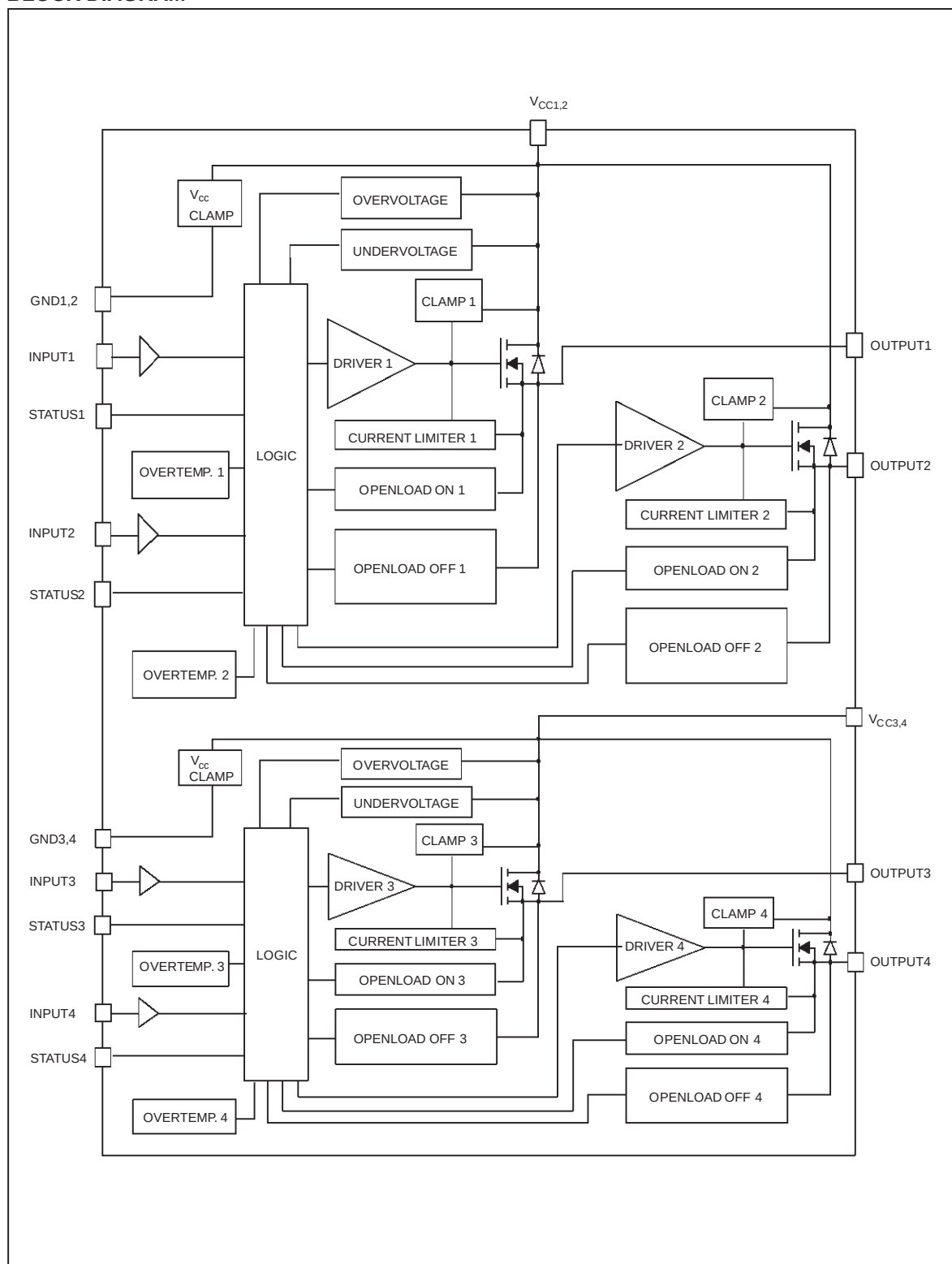
The device detects open load condition both in on and off state. The openload threshold is aimed at detecting the 5W/12V standard bulb as an openload fault in the on state. Output shorted to V_{CC} is detected in the off state. Device automatically turns off in case of ground pin disconnection.

ABSOLUTE MAXIMUM RATING

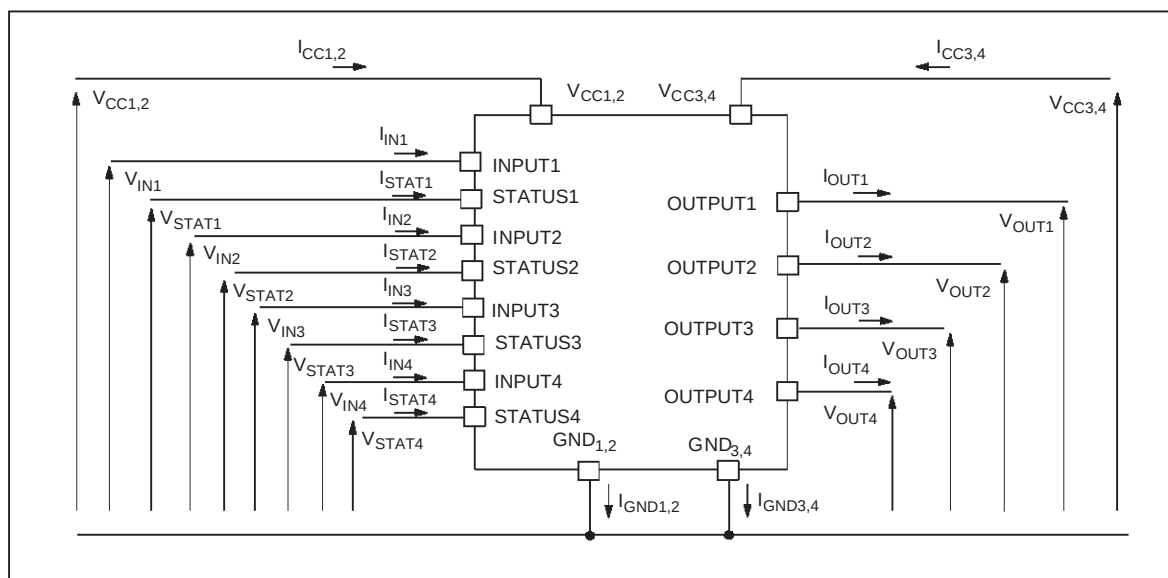
Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	41	V
- V_{CC}	Reverse DC Supply Voltage	- 0.3	V
- I_{GND}	DC Reverse Ground Pin Current	- 200	mA
I_{OUT}	DC Output Current	Internally Limited	A
- I_{OUT}	Reverse DC Output Current	- 6	A
I_{IN}	DC Input Current	+/- 10	mA
I_{STAT}	DC Status Current	+/- 10	mA
V_{ESD}	Electrostatic Discharge ($R=1.5\Omega$; $C=100pF$)	2000	V
P_{tot}	Power Dissipation $T_{pins}=25^{\circ}C$	6.25	W
T_j	Junction Operating Temperature	Internally Limited	$^{\circ}C$
T_{stg}	Storage Temperature	- 55 to 150	$^{\circ}C$

(**) See application schematic at page 9

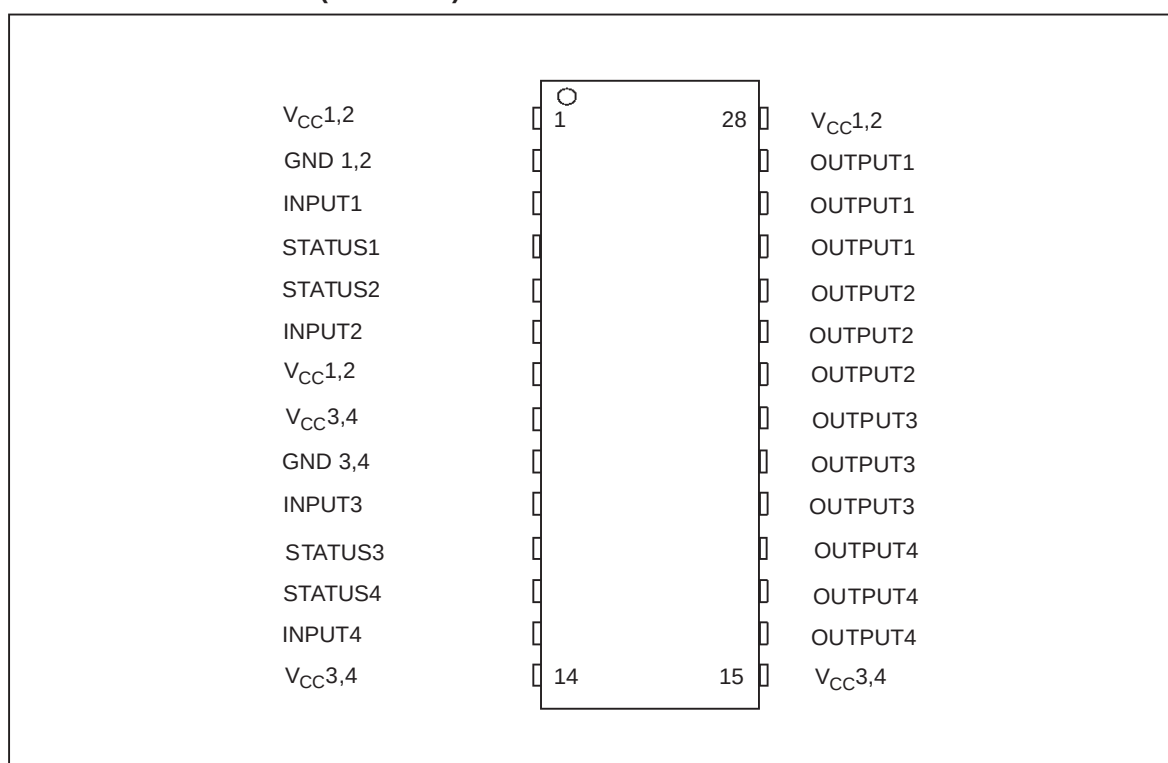
BLOCK DIAGRAM



CURRENT AND VOLTAGE CONVENTIONS



CONNECTION DIAGRAM (TOP VIEW)



VNQ830M

THERMAL DATA (Per island)

Symbol	Parameter	Value	Unit
$R_{thj-lead}$	Thermal Resistance Junction-lead per chip	20	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	70 (*)	°C/W

(*) When mounted on a standard single-sided FR-4 board with 50mm² of Cu (at least 35μm thick) connected to all V_{CC} pins.

ELECTRICAL CHARACTERISTICS (8V<V_{CC}<36V; -40°C<T_j<150°C, unless otherwise specified)

POWER OUTPUT (Per each channel)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{CC} (**)	Operating Supply Voltage		5.5	13	36	V
V _{USD} (**)	Undervoltage Shut-down		3	4	5.5	V
V _{OV} (**)	Overvoltage Shut-down		36	42	48	V
R _{on}	On State Resistance	I _{OUT} =2A; T _j =25°C I _{OUT} =2A; V _{CC} >8V			60 120	mΩ mΩ
I _S (**)	Supply Current	Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V Off State; V _{CC} =13V; V _{IN} =V _{OUT} =0V; T _j =25°C On State; V _{CC} =13V; V _{IN} =5V; I _{OUT} =0A; R _{SENSE} =3.9KΩ		12 12 5	40 25 7	μA μA mA
I _{L(off1)}	Off State Output Current	V _{IN} =V _{OUT} =0V Per each channel	0		50	μA
I _{L(off2)}	Off State Output Current	V _{IN} =0V; V _{OUT} =3.5V Per each channel	-75		0	μA

SWITCHING (Per each Channel) (V_{CC}=13V)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t _{d(on)}	Turn-on Delay Time	R _L =6.5Ω from V _{IN} rising edge to V _{OUT} =1.3V		30		μs
t _{d(off)}	Turn-off Delay Time	R _L =6.5Ω from V _{IN} falling edge to V _{OUT} =11.7V		30		μs
dV _{OUT} /dt _(on)	Turn-on Voltage Slope	R _L =6.5Ω from V _{OUT} =1.3V to V _{OUT} =10.4V		0.2		V/μs
dV _{OUT} /dt _(off)	Turn-off Voltage Slope	R _L =6.5Ω from V _{OUT} =11.7V to V _{OUT} =1.3V		0.2		V/μs

LOGIC INPUT (Per each channel)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{IL}	Input Low Level				1.25	V
I _{IL}	Low Level Input Current	V _{IN} =1.25V	1			μA
V _{IH}	Input High Level		3.25			V
I _{IH}	High Level Input Current	V _{IN} =3.25V			10	μA
V _{I(hyst)}	Input Hysteresis Voltage		0.5			V
V _{ICL}	Input Clamp Voltage	I _{IN} =1mA I _{IN} =-1mA	6	6.8 -0.7	8	V V

VCC - OUTPUT DIODE

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward on Voltage	-I _{OUT} =2A; T _j =150°C			0.6	V

(**) Per island

ELECTRICAL CHARACTERISTICS (continued)

STATUS PIN (Per each channel)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{STAT}	Status Low Output Voltage	$I_{STAT}=1.6\text{mA}$			0.5	V
I_{LSTAT}	Status Leakage Current	Normal Operation; $V_{STAT}=5\text{V}$			10	μA
C_{STAT}	Status Pin Input Capacitance	Normal Operation; $V_{STAT}=5\text{V}$			100	pF
V_{SCL}	Status Clamp Voltage	$I_{STAT}=1\text{mA}$	6	6.8	8	V
		$I_{STAT}=-1\text{mA}$		-0.7		V

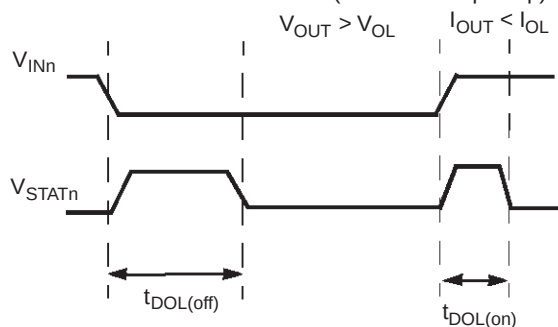
PROTECTIONS (Per each channel)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
T_{TSD}	Shut-down Temperature		150	175	200	$^{\circ}\text{C}$
T_R	Reset Temperature		135			$^{\circ}\text{C}$
T_{hyst}	Thermal Hysteresis		7	15		$^{\circ}\text{C}$
t_{SDL}	Status Delay in Overload Conditions	$T_j > T_{TSD}$			20	μs
I_{lim}	Current limitation	$5.5\text{V} < V_{CC} < 36\text{V}$	6	9	12	A
					12	A
V_{demag}	Turn-off Output Clamp Voltage	$I_{OUT}=2\text{A}$; $L=6\text{mH}$	$V_{CC}-41$	$V_{CC}-48$	$V_{CC}-55$	V

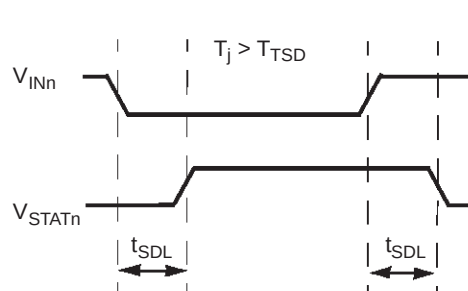
OPENLOAD DETECTION (per each channel)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_{OL}	Openload ON State Detection Threshold	$V_{IN}=5\text{V}$	0.6	0.9	1.2	A
$t_{DOL(on)}$	Openload ON State Detection Delay	$I_{OUT}=0\text{A}$			200	μs
V_{OL}	Openload OFF State Voltage Detection Threshold	$V_{IN}=0\text{V}$	1.5	2.5	3.5	V
$t_{DOL(off)}$	Openload Detection Delay at Turn Off				1000	μs

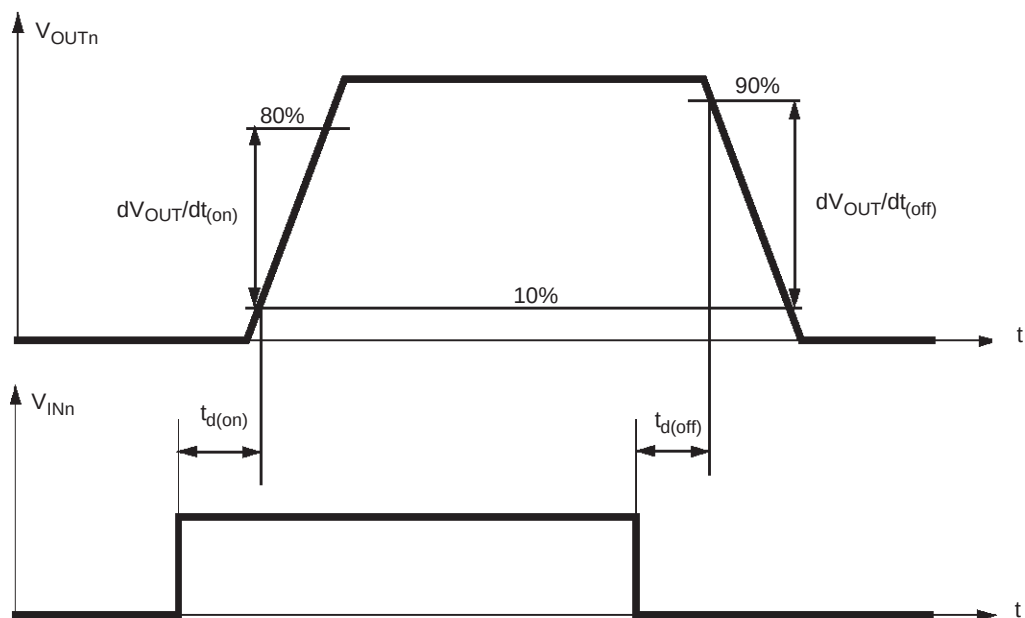
OPEN LOAD STATUS TIMING (with external pull-up)



OVER TEMP STATUS TIMING



Switching time Waveforms



TRUTH TABLE

CONDITIONS	INPUT _n	OUTPUT _n	STATUS _n
Normal Operation	L	L	H
	H	H	H
Current Limitation	L	L	H
	H	X	H
Overtemperature	L	L	H
	H	L	L
Undervoltage	L	L	X
	H	L	X
Overvoltage	L	L	H
	H	L	H
Output Voltage > V _{OLn}	L	H	L
	H	H	H
Output Current < I _{OLn}	L	L	H
	H	H	L

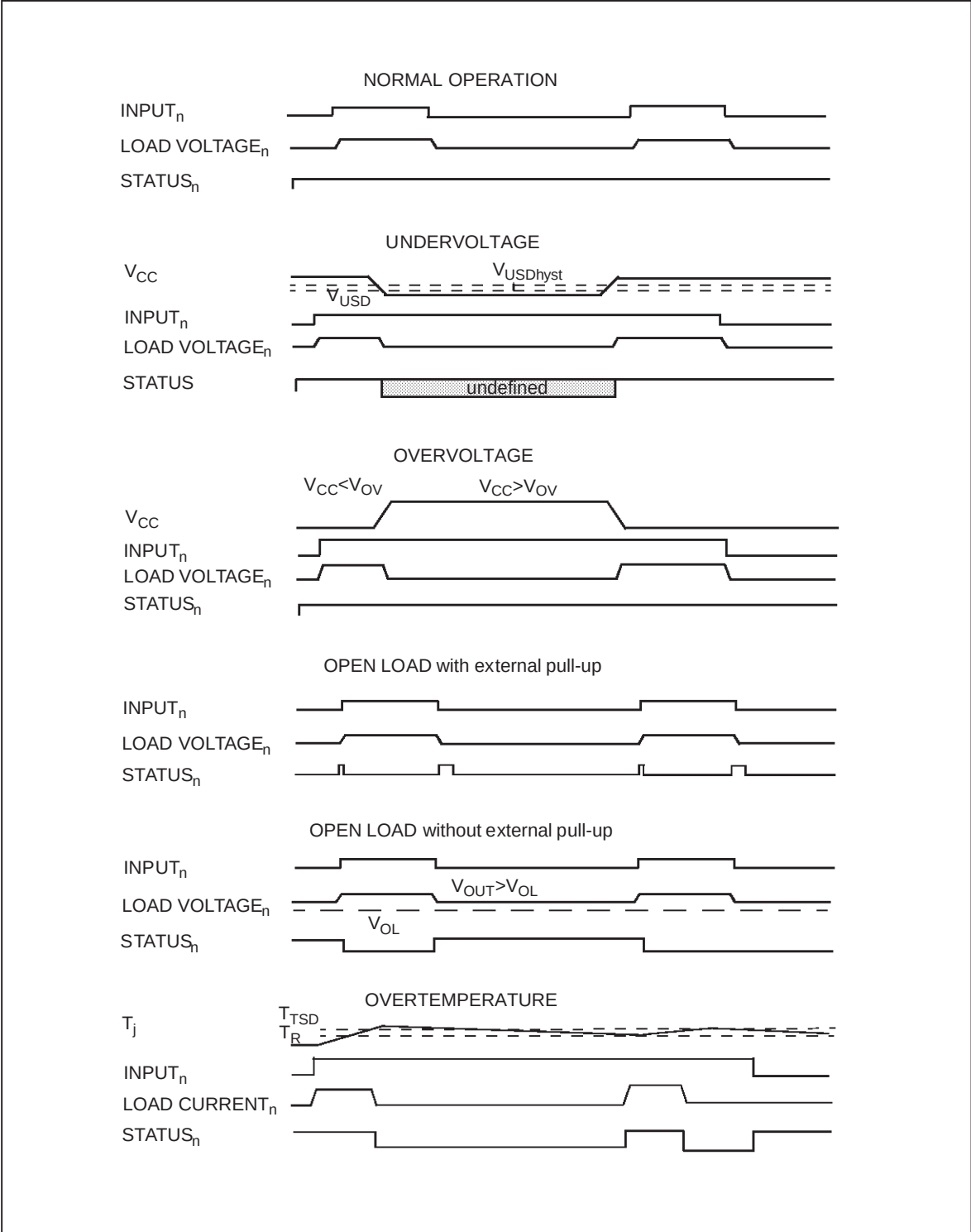
ELECTRICAL TRANSIENT REQUIREMENTS ON V_{CC} PIN

ISO T/R 7637/1 Test Pulse	TEST LEVELS				
	I	II	III	IV	Delays and Impedance
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω
3a	-25 V	-50 V	-100 V	-150 V	0.1 μ s 50 Ω
3b	+25 V	+50 V	+75 V	+100 V	0.1 μ s 50 Ω
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω

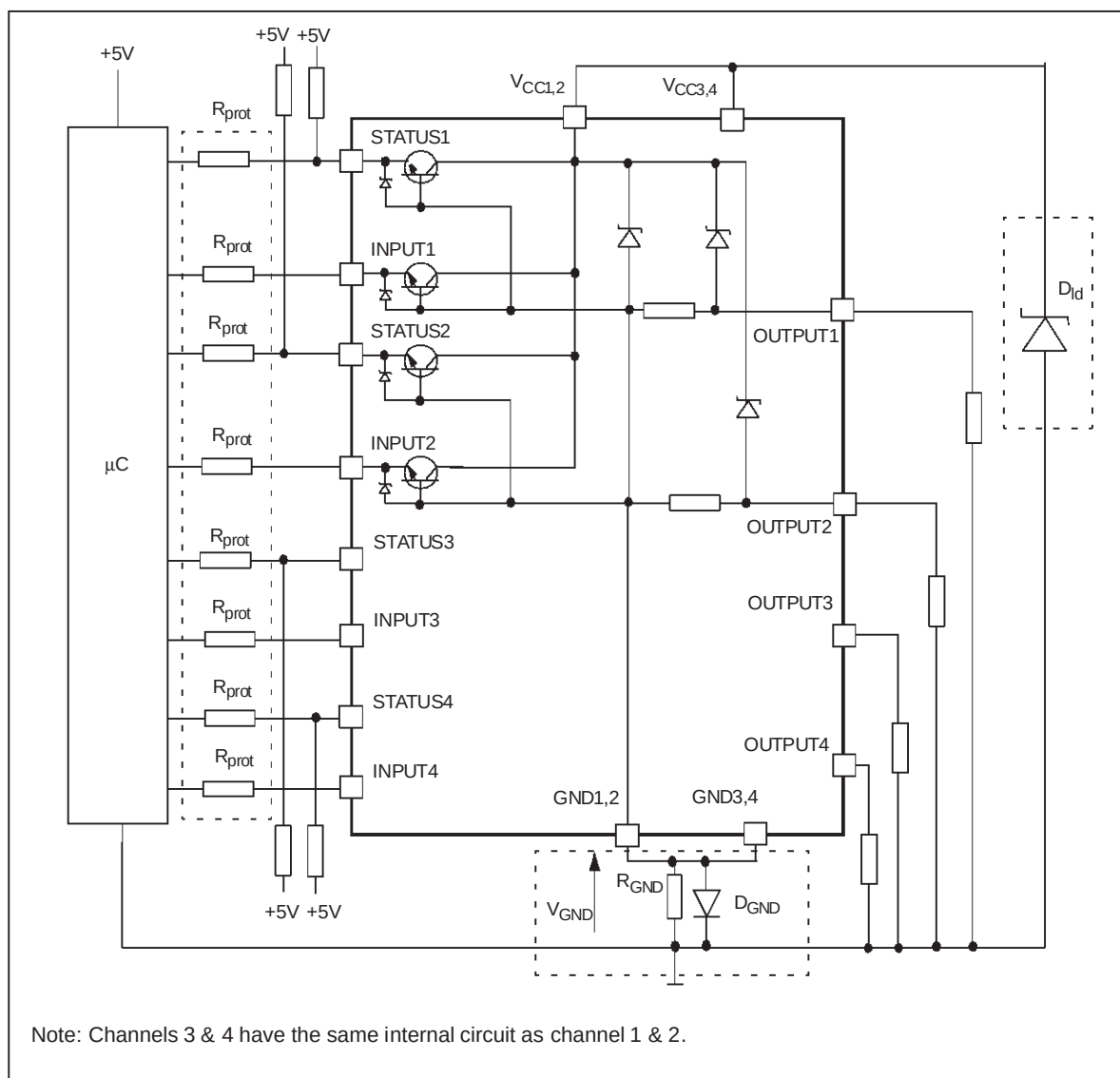
ISO T/R 7637/1 Test Pulse	TEST LEVELS RESULTS			
	I	II	III	IV
1	C	C	C	C
2	C	C	C	C
3a	C	C	C	C
3b	C	C	C	C
4	C	C	C	C
5	C	E	E	E

CLASS	CONTENTS
C	All functions of the device are performed as designed after exposure to disturbance.
E	One or more functions of the device is not performed as designed after exposure and cannot be returned to proper operation without replacing the device.

Figure1: Waveforms



APPLICATION SCHEMATIC

**GND PROTECTION NETWORK AGAINST REVERSE BATTERY**

Solution 1: Resistor in the ground line (R_{GND} only). This can be used with any type of load.

The following is an indication on how to dimension the R_{GND} resistor.

- 1) $R_{GND} \leq 600\text{mV} / 2(I_{S(on)max})$.
- 2) $R_{GND} \geq (-V_{CC}) / (-I_{GND})$

where $-I_{GND}$ is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device's datasheet.

Power Dissipation in R_{GND} (when $V_{CC} < 0$: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSD. Please note that the value of this resistor should be calculated with formula (1) where $I_{S(on)max}$ becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not common with the device ground then the R_{GND} will produce a shift ($I_{S(on)max} * R_{GND}$) in the input thresholds and the status output values. This shift will vary depending on how many devices are ON in the case of several high side drivers sharing the same R_{GND} .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then the ST suggests to utilize Solution 2.

Solution 2: A diode (D_{GND}) in the ground line.

A resistor ($R_{GND}=1k\Omega$) should be inserted in parallel to D_{GND} if the device will be driving an inductive load.

This small signal diode can be safely shared amongst several different HSD. Also in this case, the presence of the ground network will produce a shift (j 600mV) in the input threshold and the status output values if the microprocessor ground is not common with the device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

LOAD DUMP PROTECTION

D_{ld} is necessary (Transil or MOV) if the load dump peak voltage exceeds V_{CC} max DC rating. The same applies if the device will be subject to transients on the V_{CC} line that are greater than the ones shown in the ISO T/R 7637/1 table.

μC I/Os PROTECTION:

If a ground protection network is used and negative transients are present on the V_{CC} line, the control pins will be pulled negative. ST suggests to insert a resistor (R_{prot}) in line to prevent the μC I/Os pins to latch-up.

The value of these resistors is a compromise between the leakage current of μC and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of μC I/Os.

$$-V_{CCpeak}/I_{latchup} \leq R_{prot} \leq (V_{OH\mu C} - V_{IH} - V_{GND}) / I_{IHmax}$$

Calculation example:

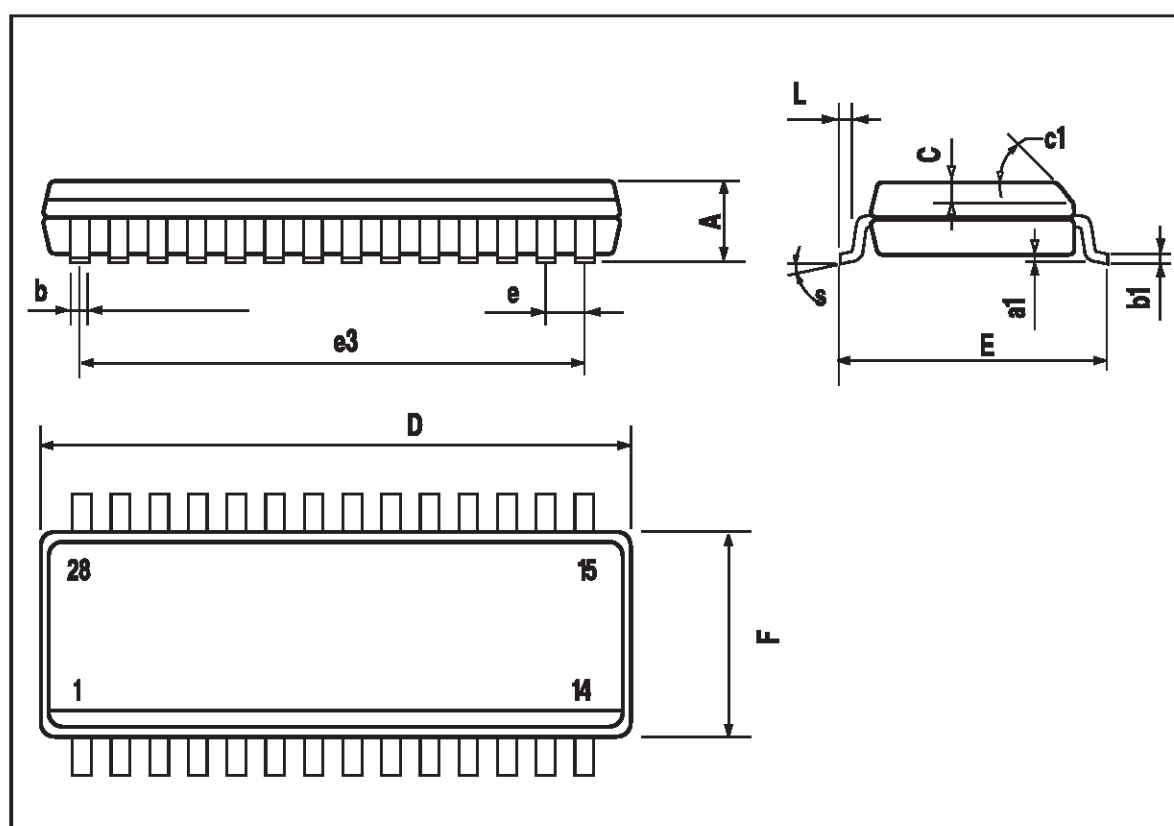
For $V_{CCpeak} = -100V$ and $I_{latchup} \geq 20mA$; $V_{OH\mu C} \geq 4.5V$

$$5k\Omega \leq R_{prot} \leq 65k\Omega.$$

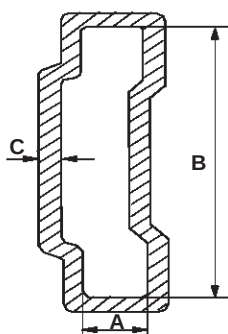
Recommended R_{prot} value is 10k Ω .

SO-28 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.30	0.004		0.012
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	17.7		18.1	0.697		0.713
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		16.51			0.650	
F	7.40		7.60	0.291		0.299
L	0.40		1.27	0.016		0.050
S	8 (max.)					



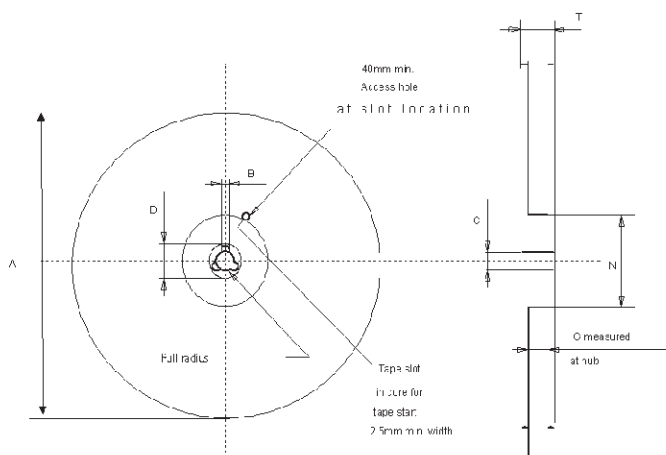
SO-28 TUBE SHIPMENT (no suffix)



Base Q.ty	28
Bulk Q.ty	700
Tube length (± 0.5)	532
A	3.5
B	13.8
C (± 0.1)	0.6

All dimensions are in mm.

TAPE AND REEL SHIPMENT (suffix "13TR")



REEL DIMENSIONS

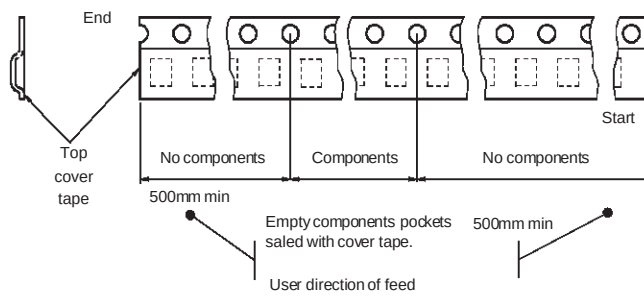
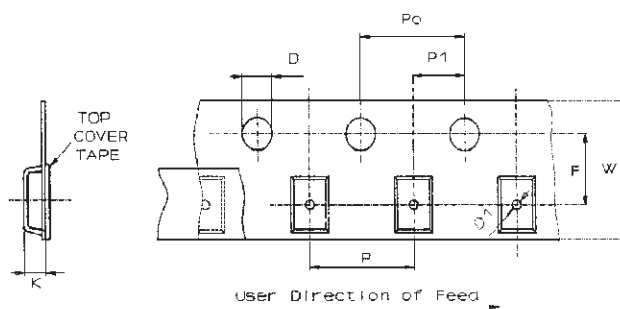
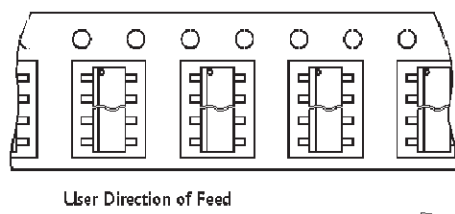
Base Q.ty	1000
Bulk Q.ty	1000
A (max)	330
B (min)	1.5
C (± 0.2)	13
F	20.2
G (+ 2 / - 0)	16.4
N (min)	60
T (max)	22.4

TAPE DIMENSIONS

According to Electronic Industries Association (EIA) Standard 481 rev. A, Feb 1986

Tape width	W	16
Tape Hole Spacing	P0 (± 0.1)	4
Component Spacing	P	12
Hole Diameter	D ($\pm 0.1/-0$)	1.5
Hole Diameter	D1 (min)	1.5
Hole Position	F (± 0.05)	7.5
Compartment Depth	K (max)	6.5
Hole Spacing	P1 (± 0.1)	2

All dimensions are in mm.



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